

3SK301 (Tentative), 3SK305 (Tentative)

Silicon N-Channel MOS

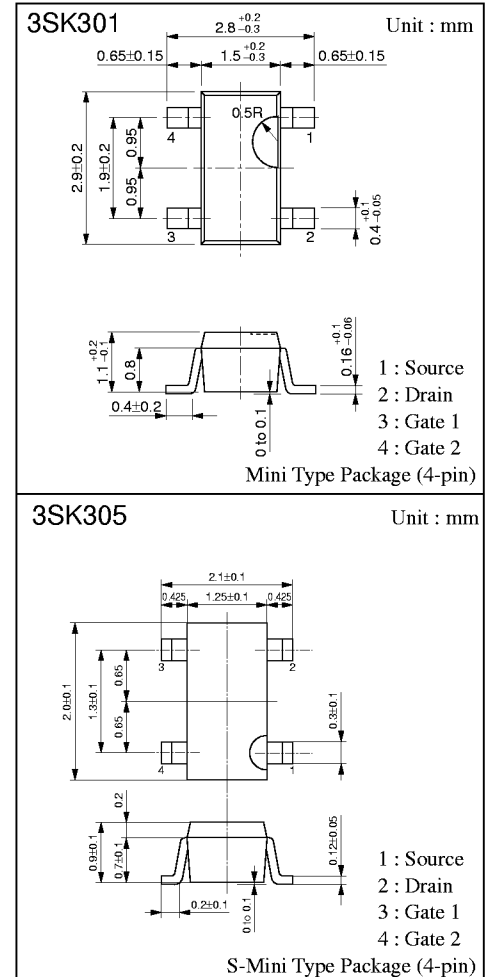
For VHF amplification

■ Features

- Though low voltage operation, performance is equivalent to the conventional product.
- Downsizing of sets by mini or S-mini type package, and automatic insertion by taping/magazine packing are available.

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Rating	Unit
Drain-Source voltage	V _{DS}	15	V
Gate 1-Source voltage	V _{G1S}	±8	V
Gate 2-Source voltage	V _{G2S}	±8	V
Drain current	I _{DS}	±30	mA
Allowable power dissipation	P _D	150	mW
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C



■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain current	I _{DS}	V _{DS} =3.5V, V _{G1S} =1.5V, V _{G2S} =3V	5	15	23	mA
Gate 1 cut-off current	I _{G1SS}	V _{DS} =V _{G2S} =0, V _{G1S} =±8V			±20	nA
Gate 2 cut-off current	I _{G2SS}	V _{DS} =V _{G1S} =0, V _{G2S} =±8V			±20	nA
Gate 1-Source cut-off voltage	V _{G1SC}	V _{DS} =3.5V, V _{G2S} =3V, I _D =100μA	0	0.6	1.3	V
Gate 2-Source cut-off voltage	V _{G2SC}	V _{DS} =3.5V, V _{G1S} =3V, I _D =100μA	0.15	0.65	1.35	V
Drain-Source voltage	V _{D SX}	I _D =50μA, V _{G1S} =-5V, V _{G2S} =0	15			V
Forward transadmittance	Y _{fs}	V _{DS} =3.5V, I _D =10mA, V _{G2S} =3V	17	23	29	mS
Input capacitance	C _{iss}	V _{DS} =10V, V _{G1S} =V _{G2S} =-5V, f=1MHz	2	2.7	3.5	pF
Output capacitance	C _{oss}		1	1.3	1.5	pF
Feedback capacitance	C _{rss}				0.02	pF
Power gain	PG	V _{DS} =3.5V, I _D =8mA, V _{G2S} =3V,	23.5	25.5	28.5	dB
Noise figure	NF	f=200MHz		2.3	2.6	

■ Marking

